FIG. 1

PRIOR ART

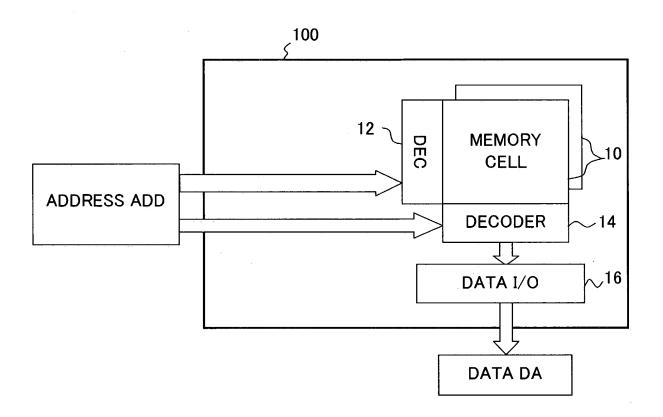
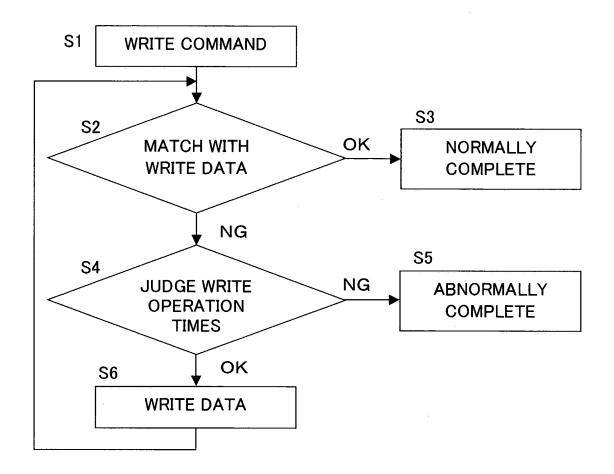
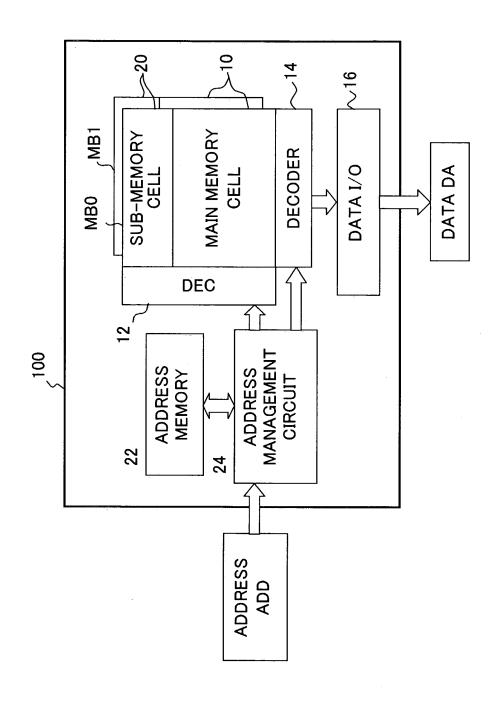


FIG. 2

PRIOR ART





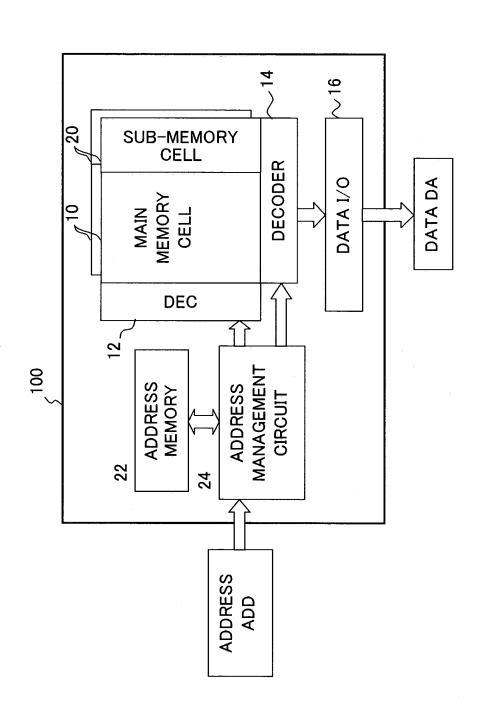
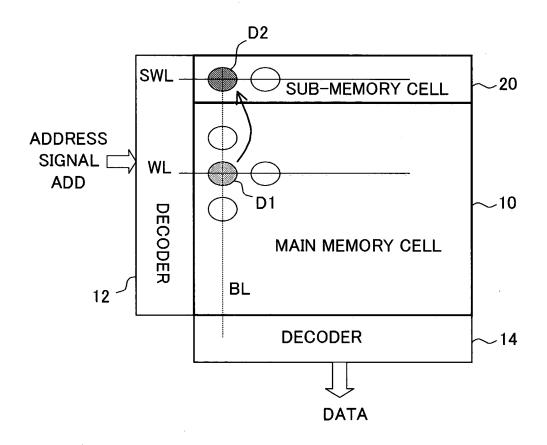


FIG. 5



Title: NONVOLATILE SEMICONDUCTOR
MEMORY HAVING PARTIAL DATA
REWRITING FUNCTION
Inventor: Tomohiro NAKAYAMA

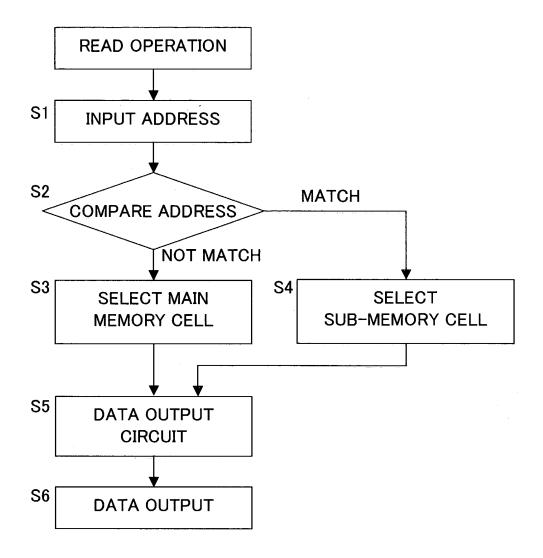
Application No. New Docket No. 108066-00085

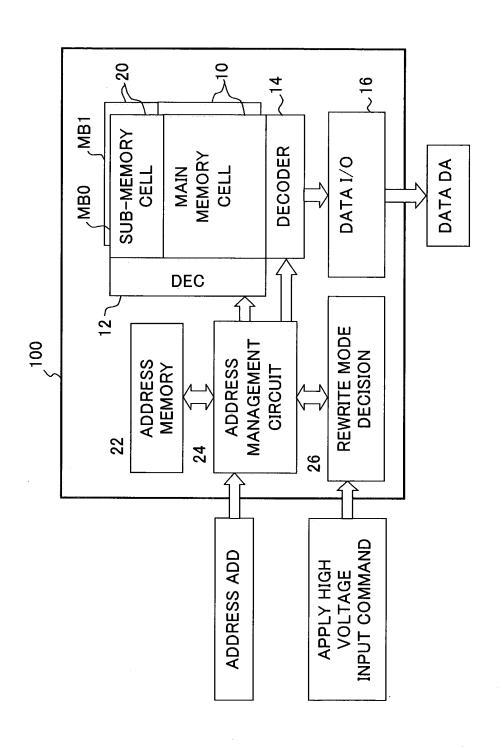
FIG. 6

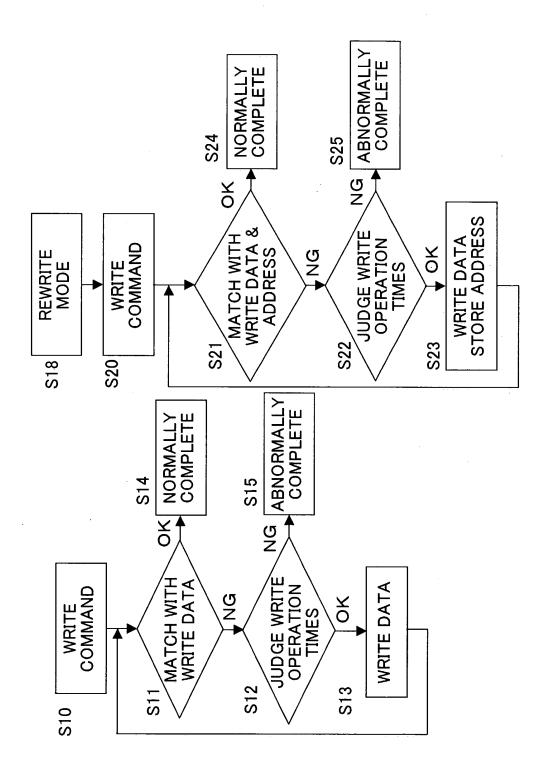
22

MAIN MEMORY ADDRESS ADD	SUB-MEMORY ADDRESS SADD
ADD1 ADD2	000 001 010 011 • • •

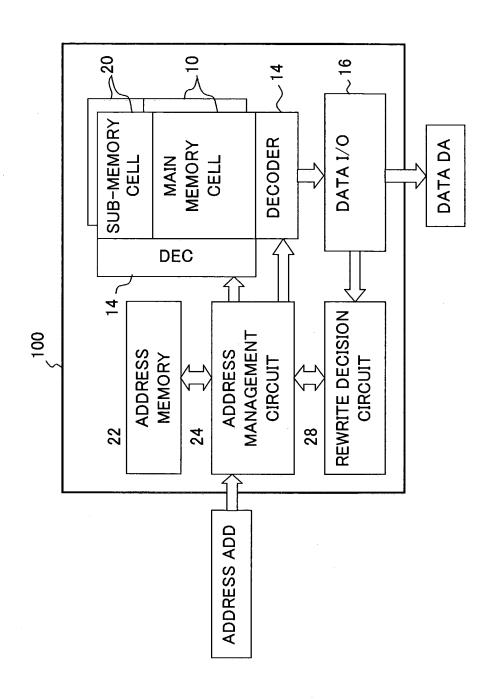
FIG. 7







-IG



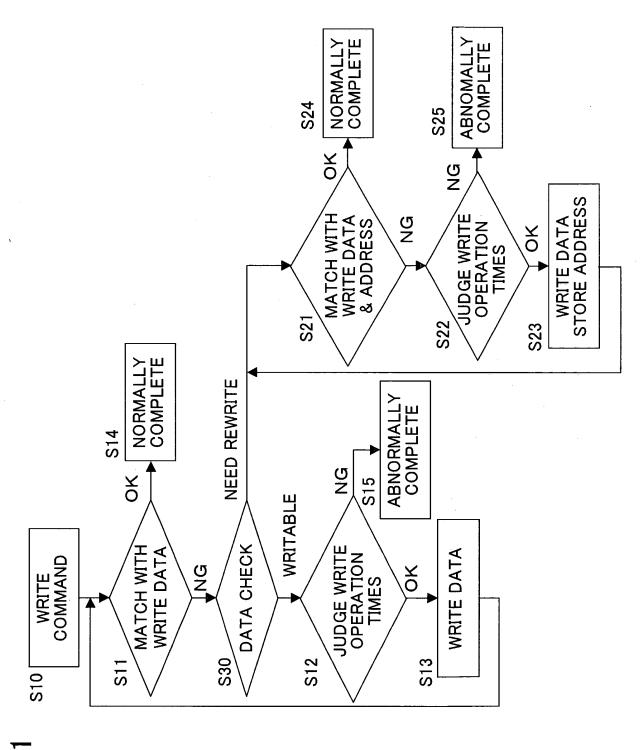


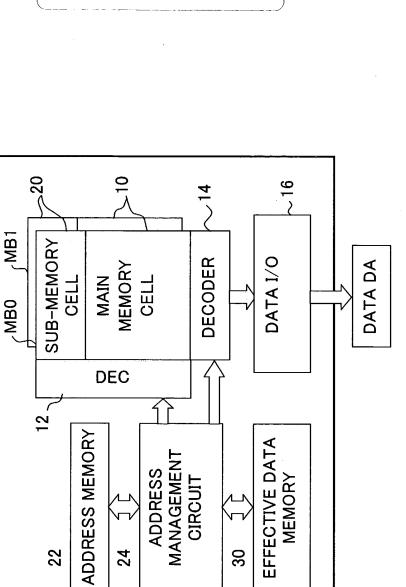
FIG. 1

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ADDRESS ADD



30

EFFECTIVE FLAG

Application No. New Docket No. 108066-00085

FIG. 13

